DG417B, DG418B, DG419B

Vishay Siliconix



ORDERING INFORMATION				
Temp Range	Package	Part Number		
DG417B, DG418B	•			
- 40 °C to 85 °C	8-Pin Plastic MiniDIP	DG417BDJ DG417BDJ-E3 DG418BDJ DG418BDJ-E3		
	0 Fin Name 2010	DG417BDY DG417BDY-E3 DG417BDY-T1 DG417BDY-T1-E3		
	8-Pin Narrow SOIC	DG418BDY DG418BDY-E3 DG418BDY-T1 DG418BDY-T1-E3		
	8-Pin MSOP	DG417BDQ-T1-E3 DG418BDQ-T1-E3		
DG419B				
	8-Pin Plastic MiniDIP	DG419BDJ DG419BDJ-E3		
- 40 °C to 85 °C	8-Pin Narrow SOIC	DG419BDY DG419BDY-E3 DG419BDY-T1 DG419BDY-T1-E3		
	8-Pin MSOP	DG419BDQ-T1-E3		

ABSOLUTE MAXIMU	M RATINGS		
Parameter		Limit	Unit
V-		- 20	
V+		20	
GND		25	V
V _L		(GND - 0.3) to (V+) + 0.3	•
Digital Inputs ^a , V _S , V _D		(V-) - 2 V to (V+) + 2 or 30 mA, whichever occurs first	
Current, (Any Terminal) Continu	ous	30	mA
Current (S or D) Pulsed at 1 ms	, 10 % Duty Cycle	100	THA THA
Storage Temperature		- 65 to 150	°C
	8-Pin Plastic MiniDIP ^c	400	
Power Dissipation (Package) ^b	8-Pin Narrow SOIC ^c	400	mW
Power Dissipation (Package)	8-Pin MSOP ^d	400	11144
	8-Pin CerDIP ^e	600	

Notes

- $a. \ Signals \ on \ S_X, \ D_X, \ or \ IN_X \ exceeding \ V+ \ or \ V- \ will \ be \ clamped \ by \ internal \ diodes. \ Limit \ forward \ diode \ current \ to \ maximum \ current \ ratings.$
- b. All leads welded or soldered to PC board.
- c. Derate 5.3 mW/°C above 75 °C.
- d. Derate 4 mW/°C above 70 °C.
- e. Derate 8 mW/°C above 75 °C.



SCHEMATIC DIAGRAM Typical Channel

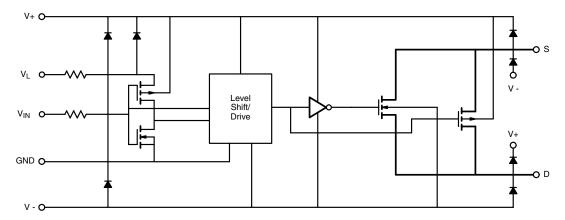


Figure 1.

SPECIFICATIONS ^a										
		Test Conditions Unless Otherwise Spec				A Suffix - 55 °C to 125 °C		D Suffix - 40 °C to 85 °C		
Parameter	Symbol	V+ = 15 V, V- = - 15 V _L = 5 V, V _{IN} = 2.4 V, 0	_	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Unit
Analog Switch	Cymbol	V - 0 V, V N - 2.4 V, 0	.0 1	remp.	Typ.		wax.	141111.	IIIux.	Oilit
Analog Signal Range ^e	V _{ANALOG}			Full		- 15	15	- 15	15	V
Drain-Source On-Resistance	R _{DS(on)}	I _S = - 10 mA, V _D = ± 12 V+ = 13.5 V, V- = - 13.		Room Full	15		25 34		25 29	Ω
	I _{S(off)}			Room Full	- 0.1	- 0.25 - 20	0.25 20	- 0.25 - 5	0.25 5	
Switch Off Leakage Current	I _{D(off)}	V+ = 16.5, V- = -16.5 V $V_D = \pm 15.5 V, V_S = \pm 15.5 V$	DG417B DG418B	Room Full	- 0.1	- 0.25 - 20	0.25 20	- 0.25 - 5	0.25 5	
	•D(оп)		DG419B	Room Full	- 0.1	- 0.75 - 60	0.75 60	- 0.75 - 12	0.75 12	nA
Channel On Leakage Current	I _{D(on)}	V+ = 16.5 V. V- = - 16.5 V	DG417B DG418B	Room Full	- 0.4	- 0.4 - 40	0.4 40	- 0.4 - 10	0.4 10	
Ç	-D(on)	$V_S = V_D = \pm 15.5 \text{ V}$	DG419B	Room Full	- 0.4	- 0.75 - 60	0.75 60	- 0.75 - 12	0.75 12	
Digital Control										
Input Current, V _{IN} Low	I _{IL}			Full		- 0.5	0.5	- 0.5	0.5	μΑ
Input Current, V _{IN} High	I _{IH}			Full		- 0.5	0.5	- 0.5	0.5	μπ
Dynamic Characteristics										
Turn-On Time	t _{ON}	$R_L = 300 \Omega$, $C_L = 35 pF$ $V_S = \pm 10 V$, See Switching	DG417B DG418B	Room Full	62		89 106		89 99	
Turn-Off Time	t _{OFF}	Time Test Circuit	DG417B DG418B	Room Full	53		80 88		80 86	ns
Transition Time	t _{TRANS}	$R_L = 300 \Omega, C_L = 35 pF$ $V_{S1} = \pm 10 V, V_{S2} = \pm 10 V$	DG419B	Room Full	60		87 96		87 93	
Break-Before-Make Time Delay	t _D	$R_L = 300 \Omega, C_L = 35 pF$ $V_{S1} = V_{S2} = \pm 10 V$ $C_L = 10 nF$	DG419B	Room	16	3		3		
Charge Injection	Q	$V_{gen} = \overline{0} V, R_{gen} = 0$	Ω	Room	38					рС
Off Isolation ^e	OIRR	$R_L = 50 \Omega, C_L = 5 pl$ f = 1 MHz	F,	Room	- 82					dB
Channel-to-Channel Crosstalk ^e	X _{TALK}		DG419B	Room	- 88					ub.

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DG417B, DG418B, DG419B

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SPECIFICATIONS ^a										
		Test Conditions Unless Otherwise Spe					uffix o 125°C	_	uffix to 85 °C	
Parameter	Symbol	V+ = 15 V, V- = - 15 V _L = 5 V, V _{IN} = 2.4 V, 0		Temp.b	Typ. ^c	Min.d	Max. ^d	Min. ^d	Max ^{d.}	Unit
Dynamic Characteristics										
Source Off Capacitance ^e	C _{S(off)}			Room	12					
Drain Off Capacitance ^e	C _{D(off)}	$f = 1 \text{ MHz}, V_S = 0 \text{ V}$	DG417B DG418B	Room	12					<u> </u>
Channel On Capacitance ^e		f = 1 MHz, V _S = 0 V	DG417B DG418B	Room	50					pF
·	C _{D(on)}		DG419B	Room	57					
Power Supplies										
Positive Supply Current	l+			Room Full	0.001		1 5		1 5	
Negative Supply Current	I-	V+ = 16.5 V, V- = - 16.5 V V _{IN} = 0 or 5 V		Room Full	- 0.001	- 1 - 5		- 1 - 5		
Logic Supply Current	ΙL			Room Full	0.001		1 5		1 5	μΑ
Ground Current	I _{GND}			Room Full	- 0.001	- 1 - 5		- 1 - 5		

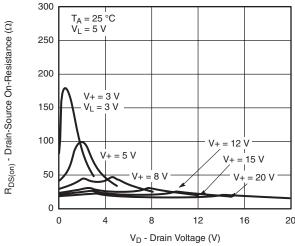
SPECIFICATIONS ^a										
		Test Conditions Unless Otherwise Spec	ified			_	uffix o 125°C		uffix to 85 °C	
Parameter	Symbol	V+ = 12 V, V- = 0 V $V_L = 5 \text{ V}, V_{IN} = 2.4 \text{ V}, 0.8$	3 V ^f	Temp.b	Typ. ^c	Min.d	Max. ^d	Min. ^d	Max. ^d	Unit
Analog Switch										
Analog Signal Range ^e	V _{ANALOG}			Full		0	12	0	12	V
Drain-Source On-Resistance	R _{DS(on)}	$I_S = -10 \text{ mA}, V_D = 3.8$ $V_{+} = 10.8 \text{ V}$	V	Room Full	26		35 52		35 45	Ω
Dynamic Characteristics										
Turn-On Time	t _{ON}	$R_L = 300 \Omega$, $C_L = 35 pF$ $V_S = 8 V$, See Switching		Room Full	100		125 155		125 143	
Turn-Off Time	t _{OFF}	Time Test Circuit		Room Full	38		66 73		66 69	ns
Break-Before-Make Time Delay	t _D	$R_L = 300 \Omega, C_L = 35 pF$	DG419B	Room	62	25		25		115
Transition Time	t _{TRANS}	$R_L = 300 \Omega, C_L = 35 p$ $V_{S1} = 0 V, 8 V, V_{S2} = 8 V,$		Room Full	95		119 153		119 141	
Charge Injection	Q	$C_L = 10 \text{ nF}, V_{gen} = 0 \text{ V}, R_{ger}$	$_{0} = 0 \Omega$	Room	18					рС
Power Supplies										
Positive Supply Current	l+			Room Full	0.001		1 5		1 5	
Negative Supply Current	I-	V+ = 13.2 V, V _L = 5.25	V	Room	- 0.001	- 1 - 5		- 1 - 5		μΑ
Logic Supply Current	Ι _L	$V_{IN} = 0 \text{ or } 5 \text{ V}$		Room	0.001		1 5		1 5	μΑ
Ground Current	I _{GND}			Room	- 0.001	- 1 - 5		-1 - 5		

Notes:

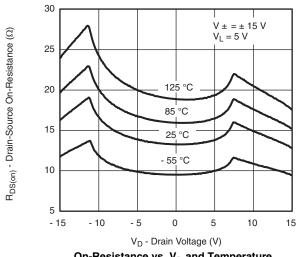
- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 °C, full = as determined by the operating temperature suffix.
 c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- e. Guaranteed by design, not subject to production test. f. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

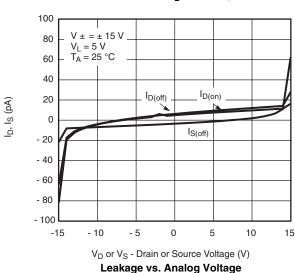
TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted



On-Resistance vs. V_D and Unipolar Power Supply Voltage

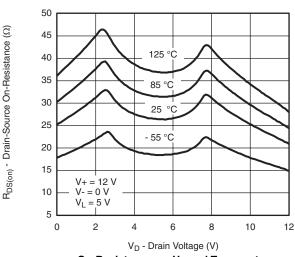


On-Resistance vs. V_D and Temperature

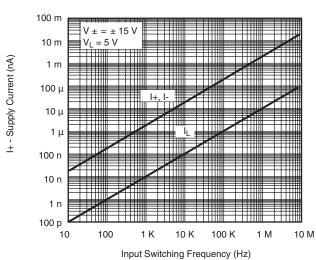


T_A = 25 °C $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain-Source On-Resistance (Ω) 35 30 25 ± 8 V 20 ± 10 V ± 12 V 15 ± 15 V 10 ± 20 V 5 0 - 20 - 15 - 10 - 5 10 15 20 5 V_D - Drain Voltage (V)

On-Resistance vs. V_D and Dual Supply Voltage



On-Resistance vs. V_D and Temperature

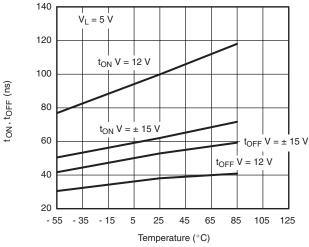


Supply Current vs. Input Switching Frequency

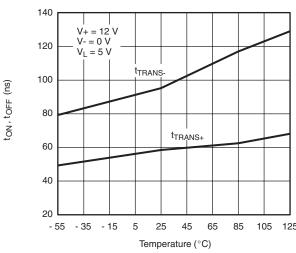
DG417B, DG418B, DG419B

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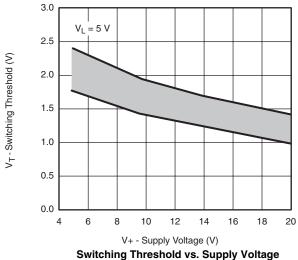
TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted

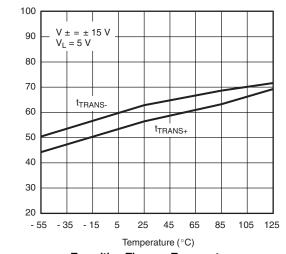


Switching Time vs. Temperature



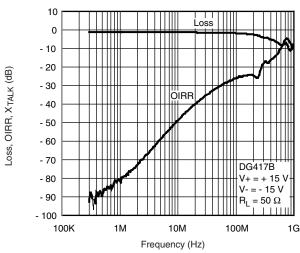
Transition Time vs. Temperature



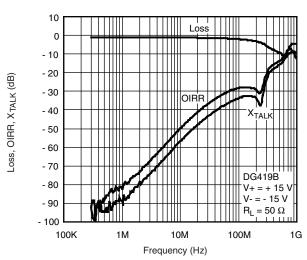


ton, toff (ns)

Transition Time vs. Temperature



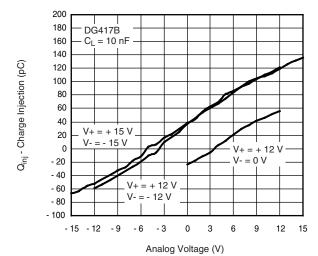
Insertion Loss, Off -Isolation Crosstalk vs. Frequency



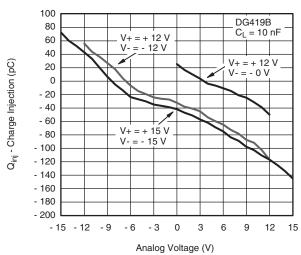
Insertion Loss, Off -Isolation Crosstalk vs. Frequency



TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted



Charge Injection vs. Analog Voltage (Measured at drain pin)

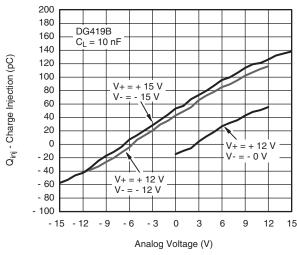


Charge Injection vs. Analog Voltage (Measured at drain pin)

180 DG417B 160 $C_L = 10 \text{ nF}$ 140 Q_{inj} - Charge Injection (pC) 120 100 80 V+ = + 15 V 60 V- = - 15 V 40 20 0 + 12 V- 20 - V- = 0 V V + = + 12 V- 40 V = -12 V- 60 - 80 - 100 - 15 - 12 - 9 - 6 0 3 6 12 15 - 3 Analog Voltage (V)

200

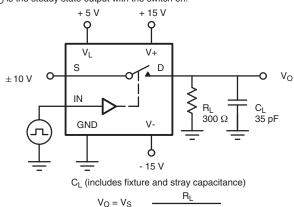
Charge Injection vs. Analog Voltage (Measured at source pin)



Charge Injection vs. Analog Voltage (Measured at source pin)

TEST CIRCUITS

 $\ensuremath{\text{V}}_{\ensuremath{\text{O}}}$ is the steady state output with the switch on.



Logic Input 0 V 0

Note: Logic input waveform is inverted for switches that have the opposite logic sense.

Figure 2. Switching Time (DG417B/418B)

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TEST CIRCUITS

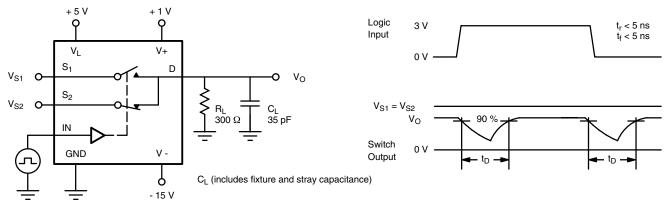
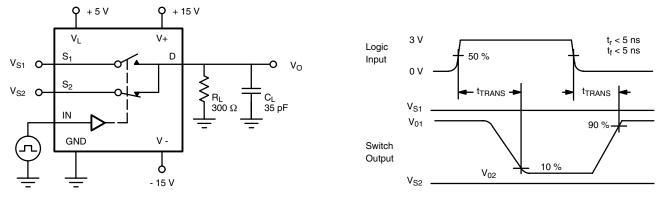


Figure 3. Break-Before-Make (DG419B)



C_L (includes fixture and stray capacitance)

$$V_O = V_S$$
 $R_L + r_{DS(on)}$

Figure 4. Transition Time (DG419B)

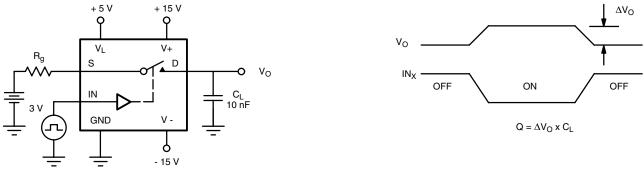


Figure 5. Charge Injection

TEST CIRCUITS

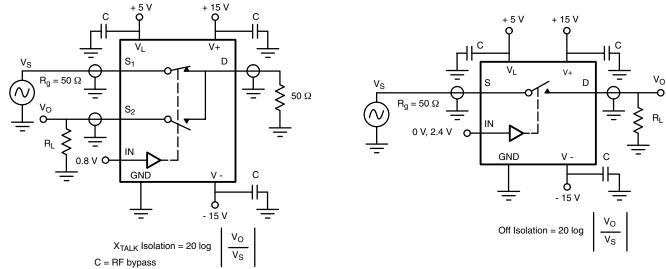


Figure 6. Crosstalk

Figure 7. Off isolation

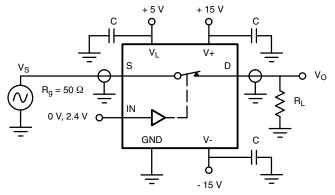


Figure 8. Insertion Loss

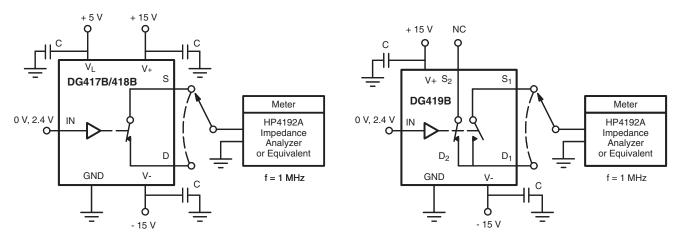
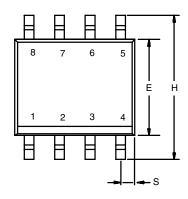


Figure 9. Source/Drain Capacitances

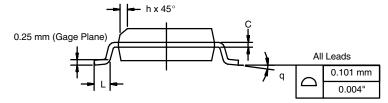
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg272107.

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES		
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050) BSC	
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-0652	27-Rev. I. 11-Sep-0	6			

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06

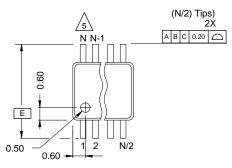




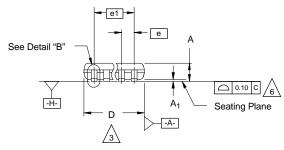


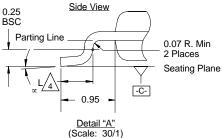
MSOP: 8-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)



Top View





NOTES:

I. Die thickness allowable is 0.203 ± 0.0127 .

2. Dimensioning and tolerances per ANSI.Y14.5M-1994.

3.

Dimensions "D" and "E $_1$ " do not include mold flash or protrusions, and are measured at Datum plane $\boxed{-H_2}$, mold flash or protrusions shall not exceed 0.15 mm per side.



Dimension is the length of terminal for soldering to a substrate.



Terminal positions are shown for reference only.



Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.



The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".



Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

9. Controlling dimension: millimeters.

10. This part is compliant with JEDEC registration MO-187, variation AA and BA.



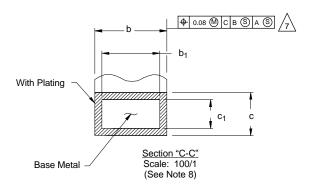
Downloaded from Arrow.com.

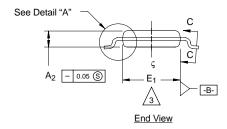
Document Number: 71244

Datums -A- and -B- to be determined Datum plane -H-.

2 Exposed pad area in bottom side is the same as teh leadframe pad size.







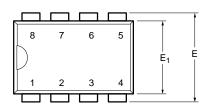
N = 8L

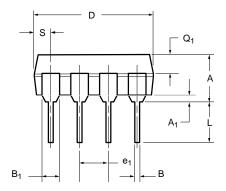
	MI	MILLIMETERS				
Dim	Min	Nom	Max	Note		
Α	-	-	1.10			
A ₁	0.05	0.10	0.15			
A ₂	0.75	0.85	0.95			
b	0.25	-	0.38	8		
b ₁	0.25	0.25 0.30 0.33				
С	0.13	-	0.23			
c ₁	0.13	0.15	0.18			
D		3.00 BSC		3		
Е		4.90 BSC				
E ₁	2.90	3.00	3.10	3		
е		0.65 BSC				
e ₁		1.95 BSC				
L	0.40	0.55	0.70	4		
N		8				
œ	0°	4°	6°			

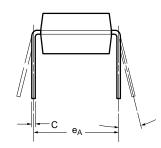
12-Jul-02



PDIP: 8-LEAD







	MILLIN	IETERS	INC	HES
Dim	Min	Max	Min	Max
Α	3.81	5.08	0.150	0.200
A ₁	0.38	1.27	0.015	0.050
В	0.38	0.51	0.015	0.020
B ₁	0.89	1.65	0.035	0.065
С	0.20	0.30	0.008	0.012
D	9.02	10.92	0.355	0.430
E	7.62	8.26	0.300	0.325
E ₁	5.59	7.11	0.220	0.280
e ₁	2.29	2.79	0.090	0.110
e _A	7.37	7.87	0.290	0.310
L	2.79	3.81	0.110	0.150
Q_1	1.27	2.03	0.050	0.080
S	0.76	1.65	0.030	0.065
ECN: S-0	3946—Rev. E	. 09-Jul-01		

DWG: 5478

15° MAX

NOTE: End leads may be half leads.

Document Number: 71259 www.vishay.com 05-Jul-01



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOT

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